

FGW85N60RB

Discrete IGBT

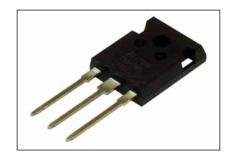
Reverse Blocking IGBT 600V / 85A

■ Features

Reverse blocking characteristic for 1 chip by Fuji's original High efficiency by applying to T-type 3 level inverter circuit.

Applications

Uninterruptible power supply Power conditioner Battery system



Equivalent circuit

○ Collector

Emitter

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings at T_i=25°C (unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	Vces	600	V	
Repetitive Peak Reverse Voltage	V _{RRM}	600	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
DC Collector Current	Ic@25	100	Α	Tc=25°C,Tj=150°C Note *1
	Ic@100	85	Α	Tc=100°C,Tj=150°C
Pulsed Collector Current	ICP	170	Α	Note *2
Turn-Off Safe Operating Area	-	170	Α	Vce≤600V,Tj≤150°C
Short Circuit Withstand Time	tsc	10	μs	Vcc≤300V,VcE=15V Tj≤150°C
IGBT Max. Power Dissipation	P _{D_IGBT}	600	W	Tc=25°C
Operating Junction Temperature	Tj	-40 ~ +150	°C	
Storage Temperature	T _{stg}	-55 ~ +150	°C	

Note *1 : Current value limited by bonding wire.

Note *2 : Pulse width limited by Tjmax.

● Electrical characteristics at T_j= 25°C (unless otherwise specified)

Description	Symbols	Conditions		Characteristics			Units			
<u> </u>	Symbols			min.	typ.	max.	Units			
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	$I_C = 1mA$, $V_{GE} = 0V$		600	-	-	V			
Zero Gate Voltage Collector Current	Ices	Vce = 600V, Vce = 0V	T _i =25°C	-	-	250	μA			
		, , , , ,	T _j =150°C	-	-	10	mA			
Gate-Emitter Leakage Current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA			
Gate-Emitter Threshold Voltage	V _{GE (th)}	V _{CE} = +20V, I _C = 85mA		5.5	6.5	7.5	V			
Collector-Emitter Saturation Voltage	V _{CE (sat)}		T _j =25°C	-	2.45	2.80	V			
	Cies	V _{CF} =10V	T _j =150°C	-	2.95 5100	-	+			
Input Capacitance	Cies	V _{CE} =10V V _{GF} =0V		-		-				
Output Capacitance		V _{GE} =UV f=1MHz		-	1150	-	pF			
Reverse Transfer Capacitance	Cres			-	740	-				
Gate Charge	Q _G	V _{CC} = 400V I _C = 85A V _{GE} = 15V		-	300	-	nC			
Turn-On Delay Time	t _{d(on)}	T _j = 25°C		-	35	-				
Rise Time	t	Vcc = 400V		-	85	-				
Turn-Off Delay Time	t _{d(off)}	Ic = 85A	-	175	-	ns				
Fall Time	tr	V _{GE} = ±15V	-	64	-					
Turn-On Energy	Eon	$R_G = 10\Omega$	-	4.7	-					
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" and F (FDRW30S120J) reverse recov	-	2.4	-	mJ				
Turn-On Delay Time	t _{d(on)}	T _i = 150°C	-	30	-	ns				
Rise Time	t	Vcc = 400V	-	125	-					
Turn-Off Delay Time	t _{d(off)}	Ic = 85A	-	185	-					
Fall Time	tr	V _{GE} = ±15V	-	66	-					
Turn-On Energy	Eon	$R_G = 10\Omega$	-	6.0	-	mJ				
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" and F (FDRW30S120J) reverse recov	-	3.0	-					
Reverse Recovery Time t		V _{cc} = 400V I _c = 85A V _{GE} = ±15V	T _j =25°C	-	165	-	no			
	L rr	R _G = ±15V R _G = 30Ω L = 500μH	T _i =150°C	-	330	-	ns			

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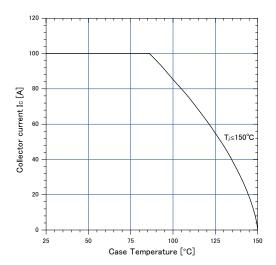
http://www.fujielectric.com/products/semiconductor/

● Thermal Resistance

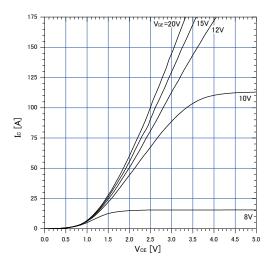
Description	Symbols	min.	typ.	max.	Units
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	50	°C/W
Thermal Resistance, Junction to Case	R _{th(j-c)}	-	-	0.208	C/VV

■ Characteristics (Representative)

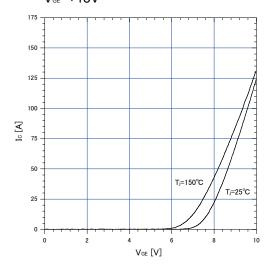
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 150$ °C



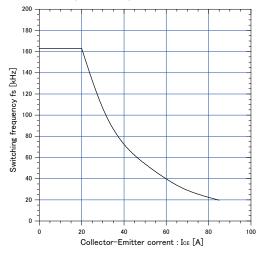
Graph.3
Typical Output Characteristics (VcE-lc)
T,=25°C



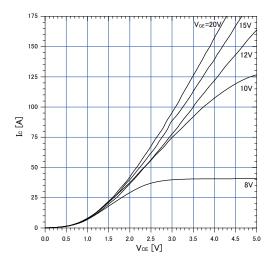
Graph.5 Typical Transfer Characteristics V_{GE} =+15V



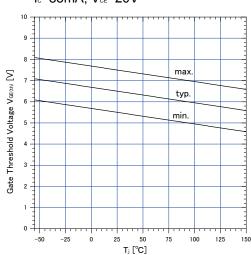
Graph.2 Collector Current vs. switching frequency V_{GE} =+15V/-15V, T_{C} ≤150°C, V_{CC} =400V, D=0.5, R_{G} =10 Ω , T_{C} =100°C



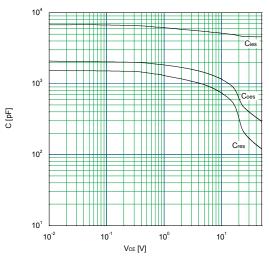
Graph.4
Typical Output Characteristics (V_{c∈}-I_c)
T_i=150°C



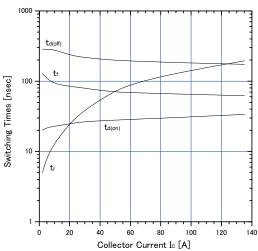
Graph.6
Gate Threshold Voltage vs. T₁
I₀=85mA, V₀=20V



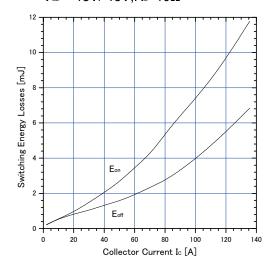
Graph.7 Typical Capacitance V_{c∈}=0V,f=1MHz,T,=25°C



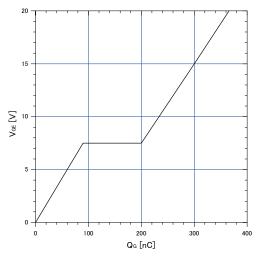
Graph.9 Typical switching time vs. I_c T_J=150°C,V_{cc}=400V,L=500 μ H V_{GE}=+15V/-15V,R_o=10 Ω



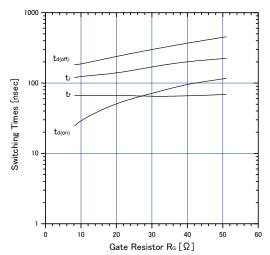
Graph.11 Typical switching losses vs. I_c T_i=150°C,V_{cc}=400V,L=500 μ H V_{cc}=+15V/-15V,R_c=10 Ω



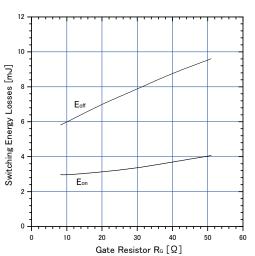
Graph.8 Typical Gate Charge V∞=400V,I₀=85A,T₀=25°C



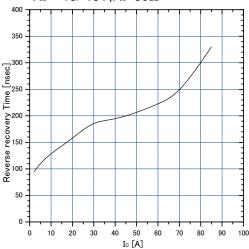
Graph.10
Typical switching time vs. R_s
T_i=150°C,V_{cc}=400V,I_c=85A,L=500μH
V_{se}=+15/-15V



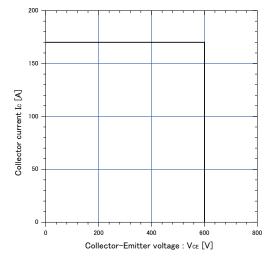
Graph.12
Typical switching losses vs. R_s
T_i=150°C,V_{cc}=400V,I_c=85A,L=500μH
V_{se}=+15/-15V



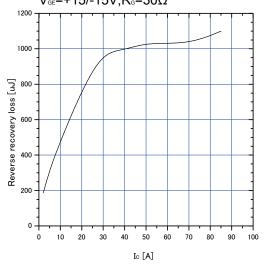
Graph.13 Typical reverse recovery time vs. Io T_i =150°C, V_{cc} =400V,L=500 μ H V_{ee} =+15/-15V, R_{e} =30 Ω



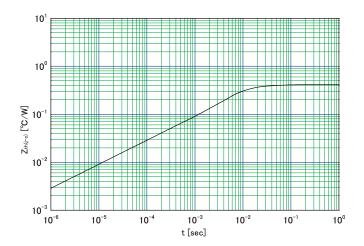
Graph.15
Reverse biased Safe Operating Area $T_1 \le 150^{\circ}\text{C}, V_{\text{GE}} = +15\text{V}/0\text{V}, R_{\text{G}} = 10\Omega$



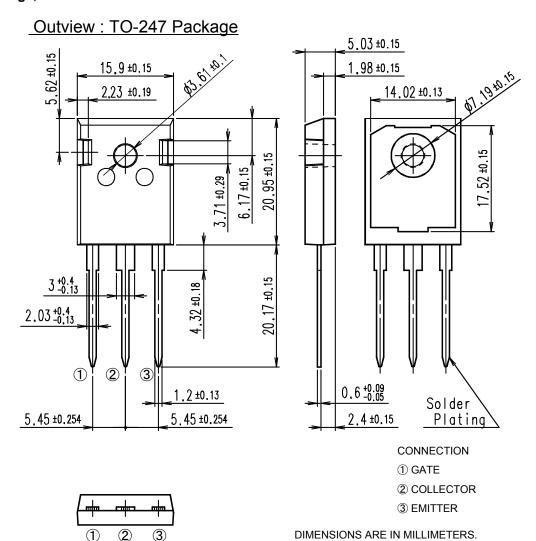
Graph.14
Typical reverse recovery loss vs. Io $T_i=150^{\circ}C,V_{cc}=400V,L=500\mu H$ $V_{ce}=+15/-15V,R_{c}=30\Omega$



Graph.16
Transient thermal resistance



■ Outline Drawings, mm



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- Measurement equipment

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- Personal equipment Industrial robots etc.

Trunk communications equipment

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